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Supporting Information

Facile rearrangement of molecular layer deposited metalcone thin film by electron beam irradiation for area selective atomic layer deposition

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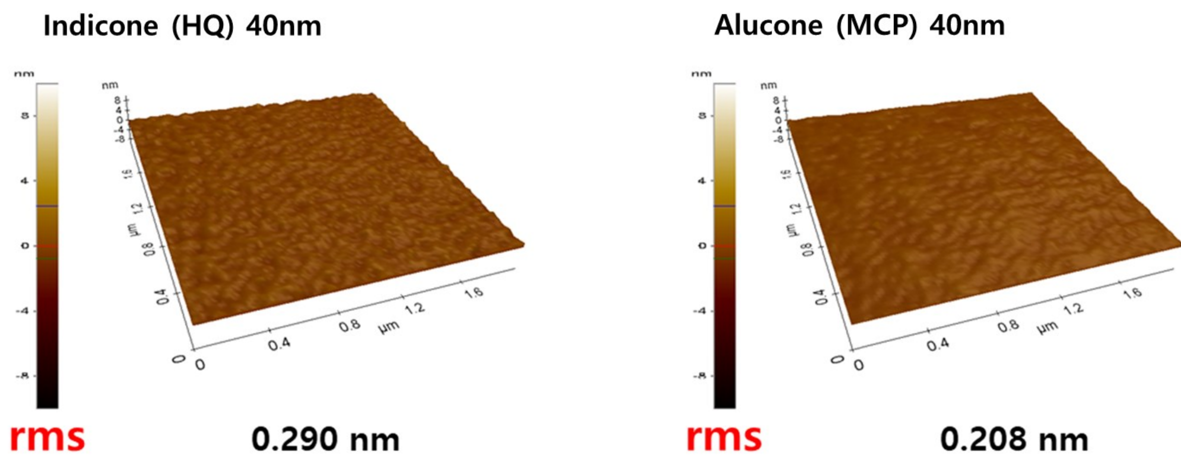

Figure S1. AFM roughness of indicone (HQ) and alucone (4MP) films grown on a Si wafer.

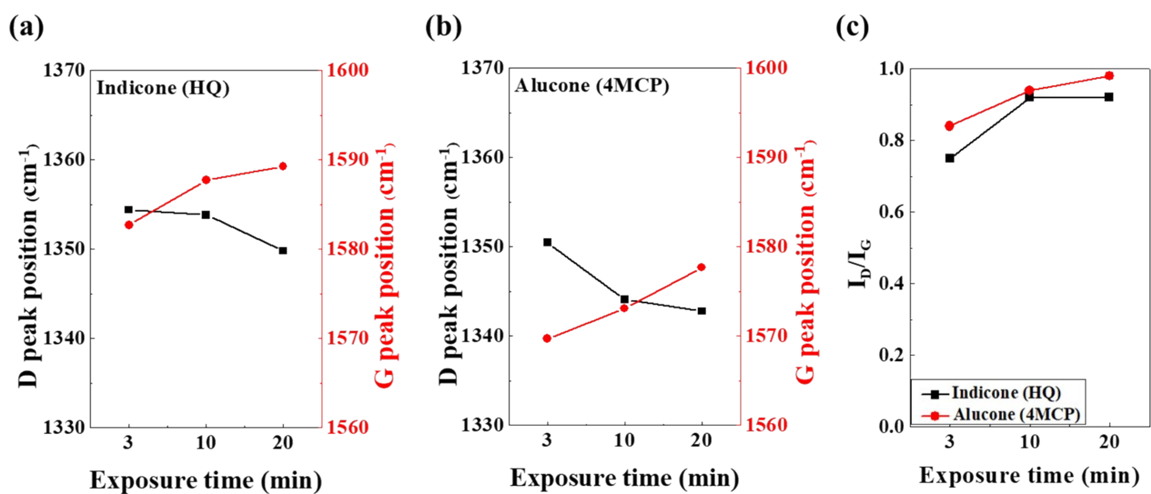

Figure S2. Shift of G band position in (a) indicone (HQ), and (b) alucone (4MP). (c) Intensity ratio of D and G peak in indicone (HQ) and alucone (4MP)